



MJ N-Channel Enhancement Mode Power MOSFET

Description

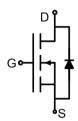
The MJ2302 uses advanced trench technology to provide excellent R_{DS(ON)}, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

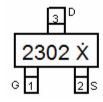
General Features

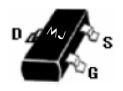
- $V_{DS} = 20V, I_{D} = -4A$ $R_{DS(ON)} < 59m\Omega @ V_{GS} = 2.5V$ $R_{DS(ON)} < 45m\Omega @ V_{GS} = 4.5V$
- High power and current handing capability
- ◆ Lead free product is acquired
- ◆ Surface Mount Package

Application

- Battery protection
- ◆ Load switch
- ◆ Power management







Schematic diagram

Marking and pin Assignment

SOT-23 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size Tape width		Quantity	
2302 X	MJ2302	SOT23	Ø180mm	8 mm	3000 units	

Absolute Maximum Ratings (Tc =25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	VDS	20	V	
Gate-Source Voltage	VDS	±12	V	
Drain Current-Continuous	lo	4	А	
Pulsed Drain Current (Note 1)	IDM	10	А	
Maximum Power Dissipation	PD	1	W	
Operating Junction and Storage Temperature Range	Тл ,Tsтg	-55 To 150	°C	

Thermal Characteristic

Thermal Resistance,Junction-to-Ambient (Note 2)	RөJA	125	°C/W
---	------	-----	------





Electrical Characteristics (TA =25°Cunless otherwise noted)

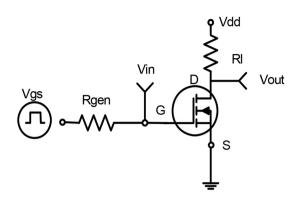
Parameter	Symbol	Condition	Min	Тур	Max	Uni
Off Characteristics	'					
Drain-Source Breakdown Voltage	BVpss	V _{GS} =0V I _D =250µA	20	22	-	V
Zero Gate Voltage Drain Current	Ipss	V _{DS} =20V,V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	lgss	V _{DS} =±12V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	VGS(th)	V _{DS} =V _{GS} ,I _D =-250µA	0.5	0.85	1.2	V
Drain-Source On-State Resistance	Rds(on)	V _{GS} =2.5V, I _D =2.5A	-	37	59	mΩ
Drain-Gource Off-State Resistance	TADS(UN)	V _{GS} =4.5V, I _D =2.9A	_	30	45	mΩ
Forward Transconductance	g FS	V _{DS} =5V,I _D =2.9A	-	8	-	S
Dynamic Characteristics (Note 4)	<u> </u>					
Input Capacitance	Clss	V _{DS} =-10V,V _{GS} =0V, F=1.0MHz	-	300	-	PF
Output Capacitance	Coss		-	120	-	PF
Reverse Transfer Capacitance	Crss		-	80	-	PF
Switching Characteristics (Note 4)	·					
Turn-on Delay Time	t _{d(on)}		-	10	15	nS
Turn-on Rise Time	tr	V _{DD} =10V,I _D =2.9A	-	50	85	nS
Turn-Off Delay Time	td(off)	V _{GS} =4.5V,R _{GEN} =6Ω	-	17	45	nS
Turn-Off Fall Time	tf	-	-	10	20	nS
Total Gate Charge	Qg		-	4.0	10	nC
Gate-Source Charge	Qgs	V _{DS} =10V,I _D =2.9A, V _{GS} =4.5V	-	0.65	-	nC
Gate-Drain Charge	Q _{gd}	-	-	1.2	-	nC
Drain-Source Diode Characteristics		1		l		I.
Diode Forward Voltage (Note 3)	VsD	V _{GS} =0V,I _S =2.9A	-	0.75	1.2	V
Diode Forward Current (Note 2)	Is		-	-	4	А

Notes:

- ${\small \textcircled{1}} \ \ \text{Repetitive Rating: Pulse width limited by maximum junction temperature.}$
- ② Surface Mounted on FR4 Board, $t \le 10$ sec.
- ③ Pulse Test: Pulse Width ≤ 300 μ s, Duty Cycle ≤ 2%.
- 4 Guaranteed by design, not subject to production



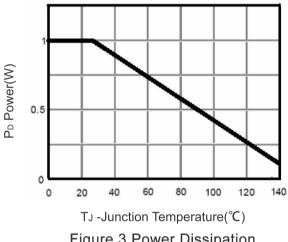
Typical Electrical and Thermal Characteristics

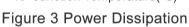


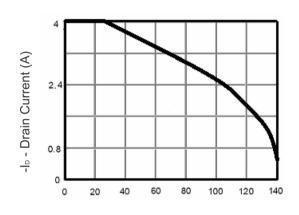
 $\mathbf{t}_{\mathsf{d(on)}}$ t_{d(off)} V_{out} **INVERTED** V_{IN} **PULSE WIDTH**

Figure 1 Switching Test Circuit

Figure 2 Switching Waveforms







T_J -Junction Temperature(°C) Figure 4 Drain Current

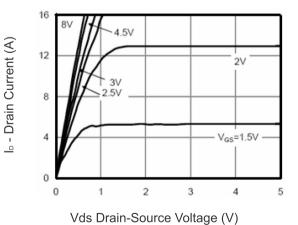


Figure 5 Output Characteristics

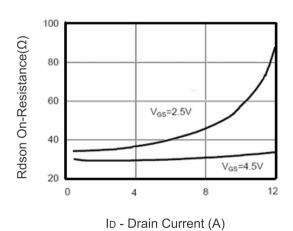


Figure 6 Drain-Source On-Resistance

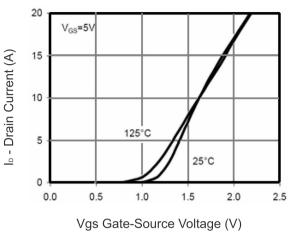
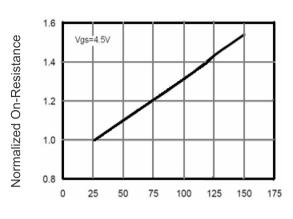


Figure 7 Transfer Characteristics



TJ -Junction Temperature(°C)
Figure 8 Drain-Source On-Resistance

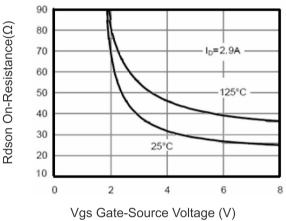
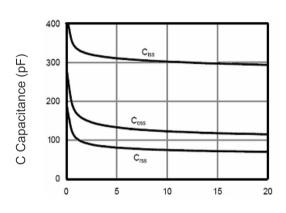


Figure 9 Rdson vs Vgs



Vds Drain-Source Voltage (V)
Figure 10 Capacitance vs Vds

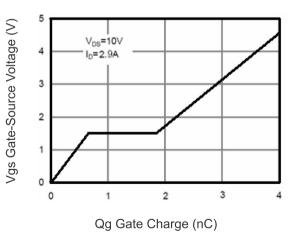


Figure 11 Gate Charge

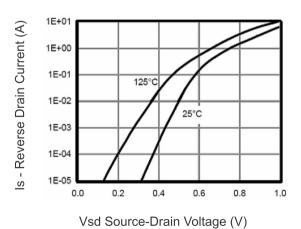
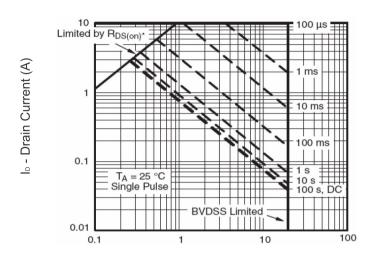


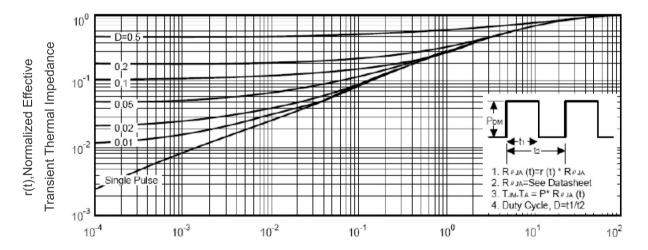
Figure 12 Source- Drain Diode Forward





Vds Drain-Source Voltage (V)

Figure 13 Safe Operation Area



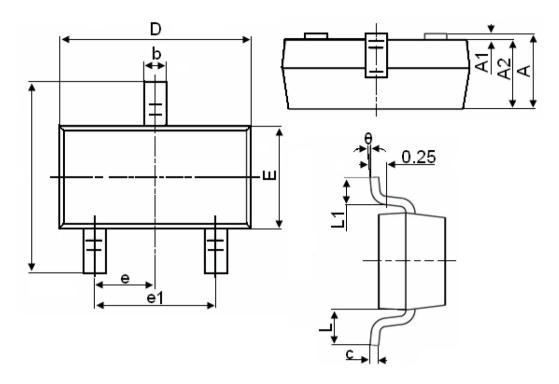
Square Wave Pluse Duration(sec)

Figure 14 Normalized Maximum Transient Thermal Impedance





SOT-23 Package Information



Symbol	Dimensions in Millimeters			
	MIN.	MAX.		
А	0.900	1.150		
A1	0.000	0.100		
A2	0.900	1.050		
b	0.300	0.500		
С	0.080	0.150		
D	2.800	3.000		
E	1.200	1.400		
E1	2.250	2.550		
е	0.950TYP			
e1	1.800	2.000		
L	0.550REF			
L1	0.300	0.500		
θ	0°	8°		

Notes:

- ① All dimensions are in millimeters.
- ${f 2}$ Tolerance ${f \pm 0.10}$ mm (4 mil) unless otherwise specified
- 3 Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4 Dimension L is measured in gauge plane.
- ⑤ Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.





Attention:

Any and all MJ power products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MJ power representative nearest you before using any MJ power products described or contained herein in such applications.

MJ power assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all MJ power products described or contained herein.

Specifications of any and all MJ power products described or contained herein stipulate the erformance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

MJ power Semiconductor CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.

In the event that any or all MJ power products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.

No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or therwise, without the prior written permission of MJ power Semiconductor CO.,LTD.

Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. MJ power believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.

Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the MJ power product that you intend to use.

This catalog provides information as of Sep.2010. Specifications and information herein are subject to change without notice.